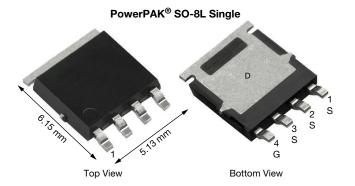
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Automotive N-Channel 60 V (D-S) 175 °C MOSFET



PRODUCT SUMMARY	
V _{DS} (V)	60
$R_{DS(on)} (\Omega)$ at $V_{GS} = 10 V$	0.0320
I _D (A) per leg	15
Configuration	Single
Package	PowerPAK SO-8L

FEATURES

- TrenchFET[®] power MOSFET
- AEC-Q101 qualified
- 100 % R_q and UIS tested
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

GO

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RoHS COMPLIANT HALOGEN FREE

ABSULUTE MAXIMU	M RATINGS (T _C = 25 °C	, unless otherwise noted)		
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-source voltage		V _{DS}	60	N/	
Gate-source voltage		V _{GS}	± 20	V	
O antinuaria ducia cumant à	T _C = 2	5°C	15	A	
Continuous drain current ^a	T _C = 1	25 °C	15		
Continuous source current (d	ode conduction) ^a	Is	15		
Pulsed drain current ^b		I _{DM}	40		
Single pulse avalanche current		I _{AS}	13		
Single pulse avalanche energy		mH E _{AS}	8.4	mJ	
1 1 1 1 1 1 1	T _C = 2	5°C	45	W	
Maximum power dissipation ^b	T _C = 1	25 °C P _D	15	vv	
Operating junction and storage	e temperature range	TJ, T _{stg}	-55 to +175		
Soldering recommendations (peak temperature) ^{d, e}			260	°C	

THERMAL RESISTANCE RATINGS					
PARAMETER		SYMBOL	LIMIT	UNIT	
Junction-to-ambient	PCB mount ^c	R _{thJA}	70	°C/W	
Junction-to-case (drain)		R _{thJC}	3.3	C/W	

Notes

b. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %

c. When mounted on 1" square PCB (FR4 material)

d. See solder profile (<u>www.vishay.com/doc?73257</u>). The PowerPAK SO-8L is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection

e. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components

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a. Package limited

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PARAMETER	SYMBOL	TES	T CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static					•		
Drain-source breakdown voltage	V _{DS}	$V_{GS} = 0 V, I_D = 250 \mu A$		60	-	-	V
Gate-source threshold voltage	V _{GS(th)}	V _{DS} =	· V _{GS} , I _D = 250 μA	2.5	3.0	3.5	v
Gate-source leakage	I _{GSS}	V _{DS} =	0 V, $V_{GS} = \pm 20 V$	-	-	± 100	nA
		$V_{GS} = 0 V$	V _{DS} = 60 V	-	-	1	
Zero gate voltage drain current	I _{DSS}	$V_{GS} = 0 V$	V _{DS} = 60 V, T _J = 125 °C	-	-	50	μA
		$V_{GS} = 0 V$	V _{DS} = 60 V, T _J = 175 °C	-	-	150	l
On-state drain current ^a	I _{D(on)}	$V_{GS} = 10 V$	$V_{DS} \ge 5 V$	5	-	-	Α
		$V_{GS} = 10 V$	I _D = 4 A	-	0.0259	0.0320	
Drain-source on-state resistance ^a	R _{DS(on)}	$V_{GS} = 10 \text{ V}$	I _D = 4 A, T _J = 125 °C	-	-	0.0527	Ω
		$V_{GS} = 10 V$	I _D = 4 A, T _J = 175 °C	-	-	0.0650	
Forward transconductance b	9 _{fs}	V _{DS}	= 15 V, I _D = 4 A	-	13	-	S
Dynamic ^b							
Input capacitance	C _{iss}		V _{DS} = 25 V, f = 1 MHz	-	508	670	pF
Output capacitance	C _{oss}	$V_{GS} = 0 V$		-	206	270	
Reverse transfer capacitance	C _{rss}			-	14	20	
Total gate charge ^c	Qg			-	7.6	12	
Gate-source charge ^c	Q _{gs}	$V_{GS} = 10 \text{ V}$ $V_{DS} = 30 \text{ V}, I_D = 3 \text{ A}$		-	2.4	-	nC
Gate-drain charge ^c	Q _{gd}			-	1.1	-	
Gate resistance	Rg		f = 1 MHz	0.5	1.1	1.7	Ω
Turn-on delay time ^c	t _{d(on)}			-	9	15	
Rise time ^c	tr	V_{DD} = 30 V, R_L = 20 Ω		-	3	10	ns
Turn-off delay time ^c	t _{d(off)}	$ \begin{array}{c c} & & & \\ \hline g & & \\ \hline g & & \\ \hline g & & \\ \hline f & & \\ f & & \\ \hline f & & \\ f & & \\ \hline f & & \\ f $		25	115		
Fall time ^c	t _f			-	6	12	
Source-Drain Diode Ratings and Charact	eristics ^b						
Pulsed current ^a	I _{SM}			-	-	40	А
Forward voltage	V _{SD}	I _F =	= 4 A, V _{GS} = 0 V	-	0.89	1.2	V
Body diode reverse recovery time	t _{rr}			-	26	60	ns
Body diode reverse recovery charge	Qrr		A di/dt 100 A/up	-	20	45	nC
Reverse recovery fall time	t _a	$I_F = 37$	A, di/dt = 100 A/μs	-	15	-	ns
Reverse recovery rise time	t _b	1		-	11	-	ns
Body diode peak reverse recovery current	I _{RM(REC)}			-	-1.45	-	Α

Notes

a. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %

b. Guaranteed by design, not subject to production testing

c. Independent of operating temperature

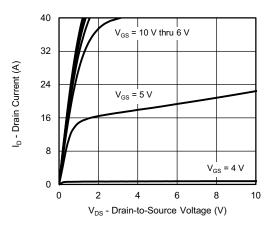
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

2

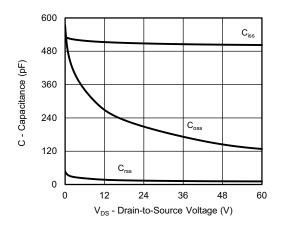


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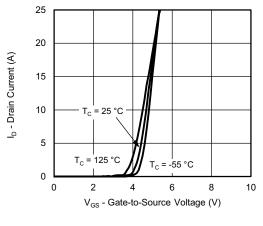
TYPICAL CHARACTERISTICS ($T_A = 25 \text{ °C}$, unless otherwise noted)



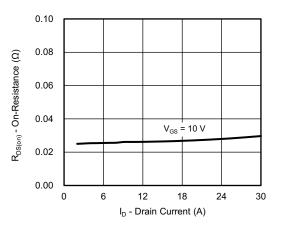
Output Characteristics



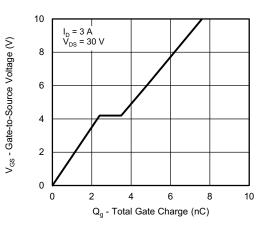
Capacitance



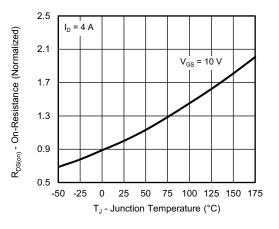
Transfer Characteristics



On-Resistance vs. Drain Current



Gate Charge



On-Resistance vs. Junction Temperature

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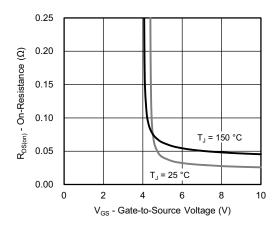
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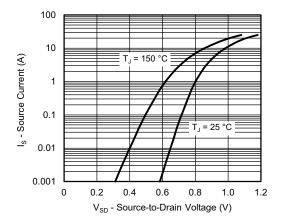
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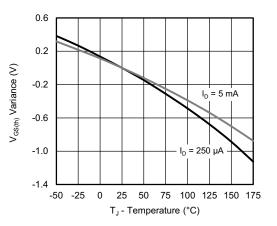
TYPICAL CHARACTERISTICS ($T_A = 25 \text{ °C}$, unless otherwise noted)



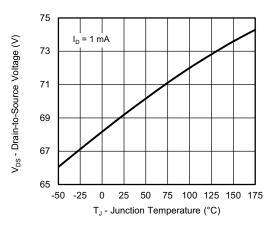
On-Resistance vs. Gate-to-Source Voltage



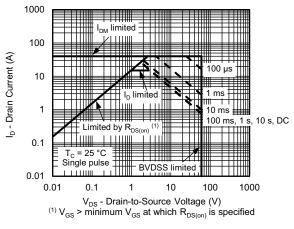
Source Drain Diode Forward Voltage



Threshold Voltage



Drain Source Breakdown vs. Junction Temperature



Safe Operating Area

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4

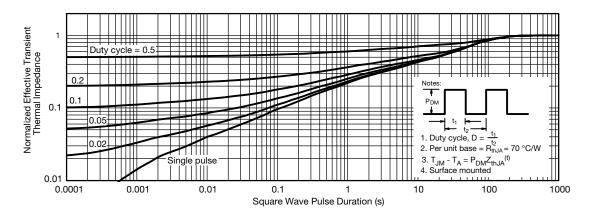
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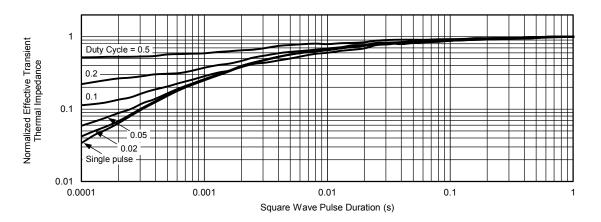
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THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

Note

• The characteristics shown in the two graphs

- Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)

- Normalized Transient Thermal Impedance Junction-to-Case (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions

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Package Information



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DIM.	MILLIMETERS			INCHES				
	MIN.	NOM.	MAX.	MIN. NOM.		MAX.		
А	1.00	1.07	1.14	0.039	0.042	0.045		
A1	0.00	-	0.127	0.00	-	0.005		
b	0.33	0.41	0.48	0.013	0.016	0.019		
b1	0.44	0.51	0.58	0.017	0.020	0.023		
b2	4.80	4.90	5.00	0.189	0.193	0.197		
b3		0.094		0.004				
b4		0.47			0.019			
С	0.20	0.25	0.30	0.008	0.010	0.012		
D	5.00	5.13	5.25	0.197	0.202	0.207		
D1	4.80	4.90	5.00	0.189	0.193	0.197		
D2	3.86	3.96	4.06	0.152	0.156	0.160		
D3	1.63	1.73	1.83	0.064	0.068	0.072		
е		1.27 BSC			0.050 BSC			
E	6.05	6.15	6.25	0.238	0.242	0.246		
E1	4.27	4.37	4.47	0.168	0.172	0.176		
E2	2.75	2.85	2.95	0.108	0.112	0.116		
F	-	-	0.15	-	-	0.006		
L	0.62	0.72	0.82	0.024	0.028	0.032		
L1	0.92	1.07	1.22	0.036	0.042	0.048		
К		0.51			0.020			
W		0.23			0.009			
W1	0.41			0.016				
W2	2.82			0.111				
W3		2.96			0.117			
θ	0°	-	10°	0°	-	10°		

Note

• Millimeters will govern



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RECOMMENDED MINIMUM PAD FOR PowerPAK[®] SO-8L SINGLE



Recommended Minimum Pads Dimensions in mm (inches)

Revision: 07-Feb-12



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